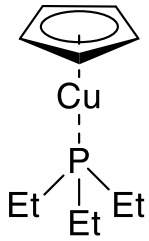
Catalog # 29-5500 Cyclopentadienyl(triethylphosphine)copper(I), min. 98%



Thermal Behavior:

- Melting point: 122-124°C [1], 127-128°C [1]; 110°C [2]
- Sublimation: 65°C/0.01 Torr [1]; 70°C/0.4-0.5 Torr [2]
- TGA diagram and data are available in [3]
- Vapor pressure: 9.75 mTorr/60°C [6]

Technical Notes:

1. CVD precursor for copper containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Cu	CVD	60°C, 90°C	10 Torr	-	158°C-250°C	4
CuI	CVD	70°C	-	I_2, C_2H_5I	20-350°C 200-350°C	5
$CuGaS_2$	CVD	65°C	37.5 Torr	$(^tBu)_2S$, $GaMe_3$	600°C	6
$CuGaSe_2$	CVD	35°C	37.5 Torr	$(^tBu)_2Se$, $GaEt_3$	400-600°C	7
$CuInSe_2$	CVD	-	-	$(^tBu)_2Se$, $InMe_3$	470°C	8

References:

1. *J. Am. Chem. Soc.* **1970**, *92*, 5114.
2. *Chem. Mater.* **1992**, *4*, 577.
3. *Thin Solid Films* **2020**, *701*, 137967.
4. *Surf. Coat. Tech.* **2007**, *201*, 9131.
5. *J. Cryst. Growth*, **2017**, *471*, 21.
6. *Thin Solid Films* **2005**, *480*, 188.
7. *J. Cryst. Growth*, **2003**, *248*, 163.
8. *Nat. Commun.* **2018**, *9*, 826.